Literature Review

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Topological insulators surface states with ferroics

1 Topological Insualtors

- 1.1 Introduction
- 1.2 Spin-Orbit Coupling

Doesn't break time-reversal symmetry like magentic field for QHE, but can lead to **quantum spin** hall effect, or QSHE, where electrons differentiated by their spin move in opposite directions. No conserved spin current to test in a material.

- 1.3 Material Growths
- 2 Magnetic Materials
- 2.1 Classifications
- 2.1.1 Ferromagnetic
- 2.1.2 Anti-ferromagnetic
- 2.1.3 Paramagnetic
- 2.1.4 Diamagnetic
- 2.2 Ferromagnetic Insualtors
- 3 TI & FI Heterostructures
- 3.1 Theory
- 3.2 Experiments

 $https://www-nature-com.ezproxy.lib.monash.edu.au/articles/nature13534\ https://advances.sciencemag.org/content/5/8/whitps://tms16.sciencesconf.org/data/pages/TI_lecture2.pdf\ https://arxiv.org/pdf/1401.0848.pdf$

4 Experimental Methods

4.1 Synthesis, Growth and Fabrication

4.1.1 MBE Growths

4.2 Metrological Methods

4.2.1 ARPES

For material characterisation, angle resolved photo-emission spectroscopy (ARPES) is a method of resolving the ejection of electrons from a material by high energy photons. Analysis of the momentum of the incident and emission resolve the electronic band structure.

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6 Knowledge & Concepts

6.1 Symmetry

Apparently ssymmetry is very important in all physical systems. For example, the order exhibited in crystals can be described through the breaking of the continuous (rotational & translational) symmetry of space. This is due to the electrostatic interactions that cause a periodic lattice. In Magnets, spin space and time reversal symmetry are broken.

6.2 Spintronics

6.2.1 Ahrimhov Bohm Effect

6.3 Fine Structure Constant

The fine structure constant, also known as Sommerfields constant, is the coupleing constant " α " that measures the strength of the EM force interacting with light.

Two methods it has been measured by include the anomalous magnetic moment of the electron, a_e , as well as appearing in the Quantum Hall Effect (QHE).

It was originally introduced by Summerfieldas a theoretical correction to the Bohr model, explaining fine structure through elliptical orbits and relitivistic mass-velocity.

6.4 Hamiltonians of Crystal Lattices

Turns out that you can describe the hamiltonian of the electrons in a crystal lattice. For this, there exists first quantisation, second quantisation hamiltonian.

- First quantisation The classical particles are assigned wave amplitudes. This is "semi-classical" where only the particles or objects are treated using quantum wavefunctions, but environment is classical.
- Second quantisation (Canonical Quantisation, occupation number representation) The wave fields are "quantized" to describe the problem in terms of "quanta" or particles. This usually means referring to a wavefunction of a state, described the the vacuum state with a series of creation operators to create the current state. Fields are now treated as field operators, similar to how physical quantities (momentum, position) are thought of as operators in first quantisation.

6.4.1 Graphene

7 Review Article Notes

7.1 J. Moore - The $Birth^{[1]}$

7.1.1 Lessons from the past

- Quantum Hall Effect can occur in 2D systems (condined) in the presence of a magentic field. It is a consequence of topological properties of the electronic wavefunctions.
- Question Can this effect arise without a large external magnetic field?
- In the 1980s, Predicted that forces from motion through crystal lattice could provide the same hall state^[2]
- The mechanism which this recently has occurred through is **spin-orbit coupling** or SOC. Spin and orbital angular momentum degrees of freedom are coupled. This coupling causes electrons to feel a spin dependent force.
- QSHE predicted in 2003. Unclear how to measure or if realistic or not. [3;4]
- Kane & Mele in 2005 produced a key theory advance, using realistic models. Showed that QSHE can survive by the use of invariants and could compute if the 2D material has an edge state or not. 2D Insulators that have 1D wires that conduct perfectly at low temps, similar to OHE. [5]
- (Hg,Cd)Te quantum wells predicted to have quantized charge conductance ^[6]. These were then picked up in 2007 ^[7].

7.1.2 Going 3D

- 2006 gave the revelation that while QHE doesn't go 2D to 3D, the TI does, subtly. [8;9;10]
- "Weak 3D TI" given through stacking of multiple 2D TIs. Not stable to disorder. A dislocation will always conains a quantum wire at the edge.
- "Strong 3D TI", connects ordinary insulators and topological insulators by breaking time-reversal symmetry. [9] This is the focus result for experimental physics at the moment.
- SOC is also required, but mixes all spins, unlike the 2D case. Spin direction dictates the momentum along the surface. Scattering also occurs, but metallic surface cannot vanish.
- First 3D TI was Bi_xSb_{1-x} . Surfaces mapped using ARPES experiment. The surface was complex, but launched a search for other TIs. [11;12].
- Heavy metal, small bandgap semiconductors are meant to be the best candidates (this sounds like TMDs haha but not implied) for two reasons.
 - SOC is relativistic, and only strong for heavy elements.
 - Large bandgaps, relative to the scale of SOC, will not allow SOC to change the phase. This is because bands either need to invert or be able to cross or change properties by local deformation (I think).
- The discovery of Bismuth Selenide Bi_2Se_3 and Bismuth Telluride Bi_2Te_3 . They exhibit TI behaviour to higher temperatures, bulk bandgaps of $> 0.1 \text{ eV}^{[13;14;15]}$.

- The large bandgap is good for measurement in higher temperature
- Simple surface states to investigate heterostructures etc.
- Complication Distinction between surface and bulk states residual conductivity resulting from impurities.
- Graphene? Bi₂Se₃ looks like Graphene, due to it's Dirac nature. The difference for graphene is that a TI has only one Dirac point. Graphene has spin degeneracy with two Dirac points. The difference is major, including applications for quantum computing. This implies that the bandstructure & reciporical lattice are really important for preserving coherent spin phenomena.
 - STMs found interference patterns near steps / defects, showing electrons aren't completely reflected - even when strong disorder occurs [16;17;18].
 - * Generally, anderson localization, the formation of insulating states, is meant to occur in materials with surface states (ie, Noble metals).
 - * TI surface states are distinguished through this property!
 - * In some 2D models, it seems to form as a result of some disorder?
 - * In graphene, apparently smooth potentials might do the same, but it's quite unlikely!
 - Femi level is located at the Dirac point for graphene! This is very adventageous, because of the tunability of the material. However, when it comes to other materials, it will not be as easy to tune the DOS around some point of interest like in graphene, without some form of doping. It was demonstrated recently in Bi₂Se₃ that you could tune to the Dirac point as well^[19]. The chemical potential is really important to be able to control for purposes like this.

7.1.3 Materials Challenges

- Two important experiments:
 - Aharonov-Bohm Effect observed in nano-ribbons
 - MBE grow thin films of Bi₂Se₃ controlling thickness.
- Items to characterize:
 - Transport & optical properties on the metalic surface to measure the spin state and conductivity.
 - Improved materials with reduced bulk conductivity may be required!

7.1.4 A Nascent Field

- Particle physics in the 1980s predicted a particle who coupled to ordinary EM fields.
- Cond.Mat Physics seek phases of matter to respond to influence.
 - Solid in response to sheer force
 - Superconductor in response to Meissner effect
 - T.I. in response to axion electrodynamics, ie in response to a scalar product **E.B.** (1980s)
 - $\ast\,$ Two coefficients correspond to OIs (ordinary) and TIs.
- \bullet Just like insulators modify dielectric constant, coefficient of ${\bf E}^2$ in Lagrangian, TI's generate non-zero coefficient of ${\bf E.B}$
- Applications are in electronics and magnetic memory, not due to speed, but rather due to reproducability and no fatigue, as a result purely from the electrons.

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7.2 title

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